2005.9

THE SPECIFICATION OF AlGaAs IR LED CHIP "IR3MH"

1. DESCRIPTION

This is a AlGaAs Infrared LED chip. It is P-side up. The peak wavelength is 870 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25℃)

CONDITION			MIN.	TYP.	MAX.	UNIT
Forward Voltage	(Vf)	IF=20mA		1.8		V
Reverse Current	(Ir)	Vr=3V			10	uA
Radiated Power[1)]	(Po)	IF=20mA		1.3		mW
Peak Wavelength	(λ p)	IF=20mA		870		nm
Cut Off Frequency	(Fc)	20±10mAp-p		75		MHz

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current : 30 mA(DC)
Reverse Voltage : 3 V(IR=10 μ A)

4. PHYSICAL CHRACTERISTICS AND STRUCTURE

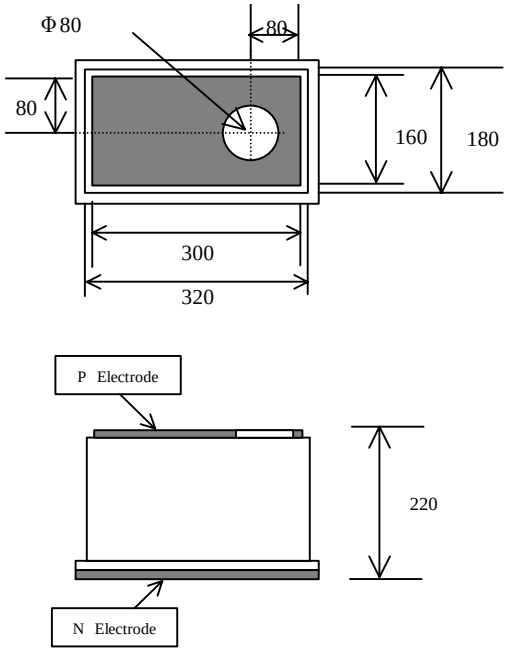
1) Material : AlGaAs
2) Structure : Double Hetero Structure
3) Junction Size : 180 μ m × 320 μ m
4) Thickness : 220 μ m
5) Emission area : 80 μ m diameter
6) Anode Metallization : Gold Alloy
7) Cathode Metallization: Gold Alloy

2005.9

Physical Dimensions

Model IR3MH

UNIT:um



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.